

AO8810-VB Datasheet

Dual N-Channel MOSFET

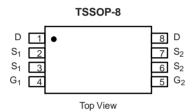
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)			
20	$0.014 \text{ at V}_{GS} = 4.5 \text{ V}$	7.6			
	0.018 at V _{GS} = 2.5 V	6.5			

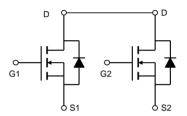
FEATURES

- Halogen-free Option Available
- Trench Power MOSFETs









ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	s otherwise n	oted		_	
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	20		V	
Gate-Source Voltage		V _{GS}	± 12		V	
0 1 0 1 7 150 00/3	T _A = 25 °C	- I _D	7.6	6.2		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		6.5	4.5	^	
Pulsed Drain Current		I _{DM}	30		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	1.5	1.0		
M · D D · · · · · · · · · · · · · · · ·	T _A = 25 °C	P _D	1.5	1.0	W	
Maximum Power Dissipation ^a	T _A = 70 °C		0.96	0.64		
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Тур.	Max.	Unit
Mariana kanting ta Andria (8	t ≤ 10 s	R _{thJA}	72	83	°C/W
Maximum Junction-to-Ambient ^a	Steady State		100	120	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	55	70	

Notes:

a. Surface Mounted on FR4 board, $t \le 10$ s.

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.



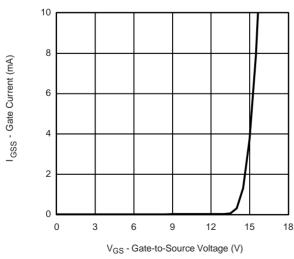
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.6		1.6	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 200	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1		
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 70 °C			25	μΑ	
On-State Drain Current ^b	I _{D(on)}	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
5 1 0 0 0 1 1 b	В	$V_{GS} = 4.5 \text{ V}, I_D = 6.5 \text{ A}$		0.014		-	
Drain-Source On-State Resistance ^b	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 5.5 \text{ A}$		0.018		Ω	
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 6.5 \text{ A}$		30		S	
Diode Forward Voltage ^b	V_{SD}	I _S = 1.5 A, V _{GS} = 0 V		0.71	1.2	V	
Dynamic ^a							
Total Gate Charge	Q_g			12	18		
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 6.5 \text{ A}$		2.2		nC	
Gate-Drain Charge	Q_{gd}			3.6			
Turn-On Delay Time	t _{d(on)}			245	365		
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		330	495		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 4.5 V, R_G = 6 Ω		860	1300	ns	
Fall Time	t _f			510	765		

Notes:

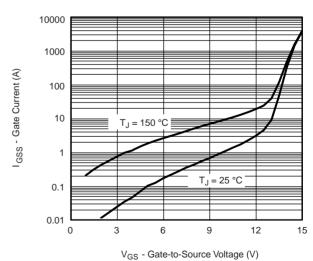
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



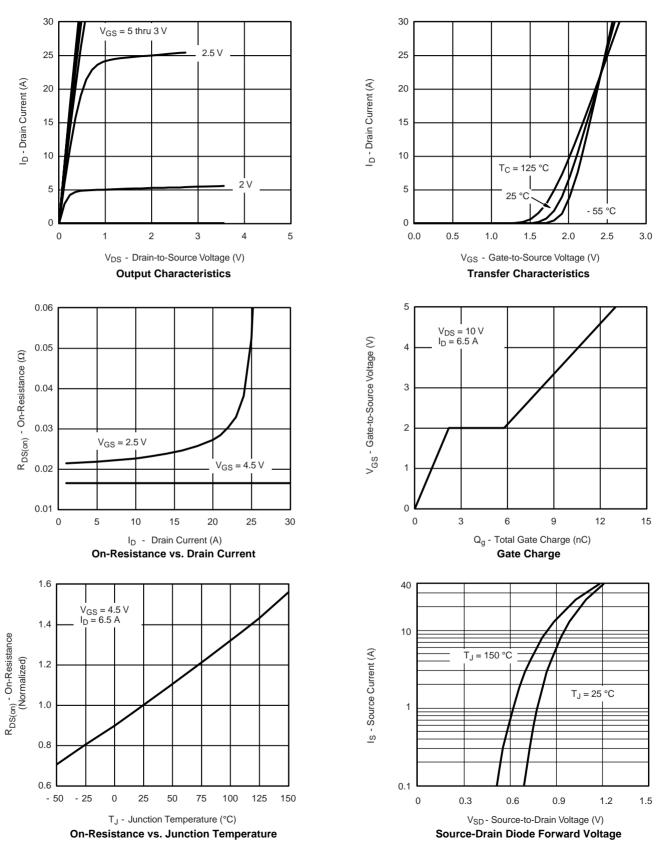




Gate Current vs. Gate-Source Voltage

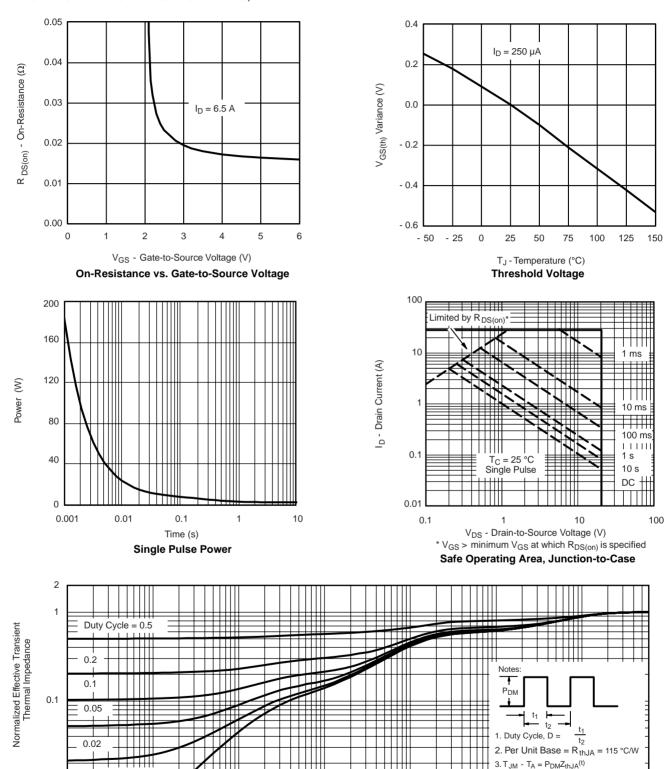


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Ambient

10-1

100

600

4. Surface Mounted

10

0.01

10-4

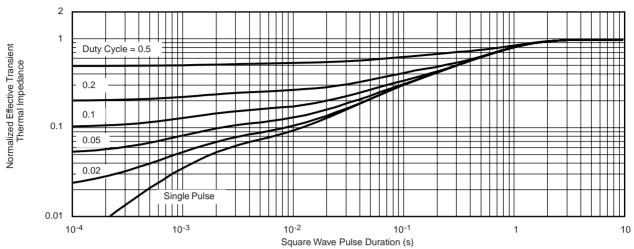
Single Pulse

10-3

10-2



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



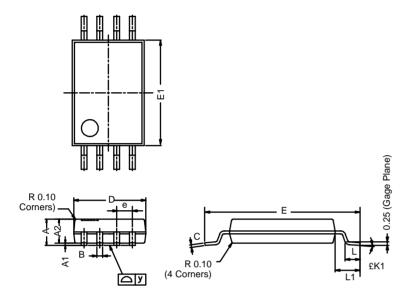
Normalized Thermal Transient Impedance, Junction-to-Foot

6



TSSOP: 8-LEAD

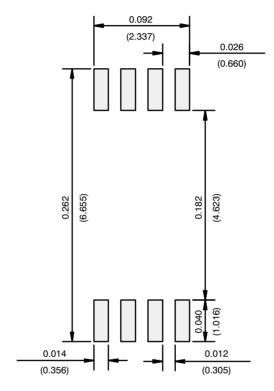
JEDEC Part Number: MO-153



	MILLIMETERS				
Dim	Min	Nom	Max		
Α	_	-	1.20		
A ₁	0.05	0.10	0.15		
A ₂	0.80	1.00	1.05		
В	0.19	0.28	0.30		
С	_	0.127	-		
D	2.90	3.00	3.10		
Е	6.20	6.40	6.60		
E ₁	4.30	4.40	4.50		
е	-	0.65	-		
L	0.45	0.60	0.75		
L ₁	0.90	1.00	1.10		
Υ	_	_	0.10		
£ K1	0°	3°	6°		
ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5844					



RECOMMENDED MINIMUM PADS FOR TSSOP-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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